

DOCKET NO.: 205890US99



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: : GROUP ART UNIT: 2811

JAMAL RAMDANI ET AL :

SERIAL NO.: 09/721,566 : EXAMINER: HU, S.

FILED: NOVEMBER 22, 2000 :

FOR: STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR
STRUCTURES AND DEVICES UTILIZING THE FORMATION OF A
COMPLIANT SUBSTRATE FOR MATERIALS USED TO FORM THE SAME

#10
9/5/02
JUR

RESTRICTION RESPONSE

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Restriction Requirement dated April 19, 2002, Applicants elect
from Species 1 and 2 the Zintl type phase material and further elect the condition wherein the
oxide buffer layer is converted into an amorphous oxide.

RECEIVED
AUG 21 2002
TECHNOLOGY CENTER 2800

REMARKS

The claims have been divided into allegedly distinct species. Applicant has elected
the Zintl type phase material and the oxide buffer layer converted into an amorphous oxide.
Applicant cannot determine from the Office Letter which Claims the Examiner indicates such
election will read on ("claims 1, 17-27, but within claims 1-4 and 15-27"). The
restriction/election requirement is traversed.

The Office Letter contains absolutely no basis for the requirement. This is manifestly